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**CERTIFICATE OF MAILING**

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*Carrie Reddick*

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**PATENT**

**Attorney Docket No. NTI-024 (745)**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application

PATENT APPLICATION

Inventor(s): Fang-Cheng Chang.

Art Unit: unknown

Application No.: 09/941,453-6364

Examiner: unknown

Filed: 8/28/2001

Title **SYSTEM AND METHOD FOR IDENTIFYING  
DUMMY FEATURES ON A MASK LAYER**

**INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Listed below or on an attached Form PTO-1449 is information known to applicant(s). A copy of each listed publication and U.S. and foreign patent, except for pending U.S. applications, is being submitted herewith, along with a concise explanation of information in a foreign language, if any, pursuant to 37 C.F.R. §1.97-1.98.

Applicants respectfully request that the listed information be considered by the Examiner and be made of record in the above-identified application. If form PTO-1449 is enclosed, the Examiner is requested to initial and return it in accordance with MPEP § 609.

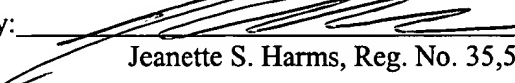
This statement is not intended to represent that a search has been made or that the information cited in the statement is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56.

- ☒ This statement qualifies under *37 C.F.R. § 1.97*, subsection (b) because (check all that apply):
- ☐ (1) It is being filed within 3 months of the application filing date and is other than a continued prosecution application under § 1.53(d)  
-- OR --
- ☐ (2) It is being filed within 3 months of entry of a national stage  
-- OR --
- ☒ (3) It is being filed before the mail date of the first Office Action on the merits.  
-- OR --
- ☐ (4) It is being filed before the mailing of a first Office Action after the filing of a request for continued examination under § 1.114
- ☐ *37 C.F.R. § 1.97(c)*. If this statement is being filed after the period specified in § 1.97(b), but before the mailing date of the earlier of a final office action under § 1.113, a notice of allowance under § 1.311, or an action that otherwise closes prosecution in the application, then:
- ☐ a certification as specified in § 1.97(e) is provided below; **or**
- ☐ a fee of \$180.00 as set forth in § 1.17(p) is authorized below, enclosed, or included with the payment of other papers filed together with this statement.
- ☐ *37 C.F.R. § 1.97(d)*. If this statement is being filed after the period specified in § 1.97(c), but on or before payment of the issue fee, then:
- A. a certification as specified in § 1.97(e) is completed below; **and**
- B. a fee of \$180.00 as set forth in § 1.17(p) is authorized below, enclosed, or included with the payment of other papers filed together with this statement.
- ☒ *Fee Authorization*. Applicant believes no fee is due. However, should a fee be found to be owing, the Commissioner is hereby authorized to charge any fees associated with this communication to Deposit Account No. 50-0574 (Docket No. NTI-024).

Respectfully submitted,

BEVER, HOFFMAN & HARMS, LLP

Dated: March 12, 2002

By:   
Jeanette S. Harms, Reg. No. 35,537

Telephone: (408) 451-5907  
Customer No. 029477

## INFORMATION DISCLOSURE



CITATION

MAR 19 2002 ETO-1449

Atty. Docket No.

NTI-024

Serial No.

09/941,453-6364

Applicant

CHANG, Fang-Cheng

Filing Date

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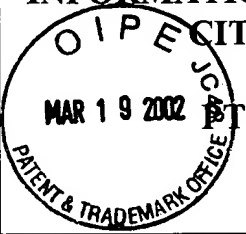
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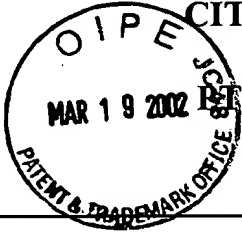
<b>INFORMATION DISCLOSURE</b> <b>CITATION</b> 		<b>Atty. Docket No.</b> NTI-024		<b>Serial No.</b> 09/941,453-6364			
		<b>Applicant</b> CHANG, Fang-Cheng		<b>Group</b> Not Yet Assigned			
		<b>Filing Date</b> 8/28/2001					
<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	WO 00/36525 A2	6/22/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67074 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67075 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67076 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>

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**INFORMATION DISCLOSURE  
CITATION**

PTO-1449

**Atty. Docket No.**

NTI-024

**Serial No.**

09/941,453-636

**Applicant**

CHANG, Fang-Cheng

**Filing Date**

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